

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A device comprising:
~~a via comprising alternating layers of dissimilar dielectric materials defining vertical on a circuit substrate, defining a via to a contact point on the circuit substrate, at least one sidewall of the via having a corrugated profile; corrugations in a wall of the via~~
; and
~~a capacitor formed on the at least one sidewall over the alternating layers of the via and coupled to the contact point, and comprising to achieve a corrugated a side wall profile corresponding to the profiling corrugated profile of the at least one sidewall.~~

2. (Currently Amended) The device of claim 1, wherein the alternating layers of dissimilar dielectric materials comprise alternating layers of silicon oxide and silicon nitride.

3-5 (Cancelled)

6. (New) The device of claim 1, further comprising a conductive metal line coupled to the capacitor, wherein, in the via the capacitor is disposed between the conductive metal line and the contact point.

7. (New) The device of claim 1, wherein the contact point comprises a first signal line, the device further comprises a second signal line coupled to the capacitor, wherein, in the via, the capacitor is disposed between the first signal line and the second signal line.

8. (New) The device of claim 7, wherein the first signal line represents a Vcc line and the second signal line a Vss line at a point of connection through the via.